

L Number	Hits	Search Text	DB	Time stamp
1	1	("5581115").PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/08 15:16
-	0	("(Sic silicon adj carbide)").PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/01 16:55
-	76801	Sic silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/04 12:32
-	423	(bipolar bjt hbt hbjt) and base with doped near5 contact and base with (opening hole recess)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/04 12:31
-	22	(Sic silicon adj carbide) and ((bipolar bjt hbt hbjt) and base with doped near5 contact and base with (opening hole recess))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/04 12:32
-	4	("4945394"   "5319220"   "5641975"   "5847414").PN.	USPAT	2004/05/01 17:18
-	25	4945394.URPN.	USPAT	2004/05/01 17:23
-	8	("4945394"   "5318915"   "5424227"   "5539217"   "5726463"   "5798277"   "5814859"   "6143593").PN.	USPAT	2004/05/01 17:25
-	1	("6194769").PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/04 11:24
-	4	((("6,218,254") or ("5,980,265") or ("5,409,859") or ("5,296,391"))).PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/04 12:10
-	3	((("5,914,611") or ("6,228,665") or ("6218254"))).PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/04 12:10
-	7	("4945394"   "5318915"   "5539217"   "5726463"   "5798277"   "5814859"   "6143593").PN.	USPAT	2004/05/04 12:11
-	25	4945394.URPN.	USPAT	2004/05/04 12:14
-	8	5350699.URPN.	USPAT	2004/05/04 12:18
-	781	(bipolar bjt hbt hbjt) and base with doped near5 contact	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/08 09:30
-	76866	Sic silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/04 12:32
-	54	((bipolar bjt hbt hbjt) and base with doped near5 contact ) and (Sic silicon adj carbide )	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/04 14:43
-	22	(Sic silicon adj carbide) and ((bipolar bjt hbt hbjt) and base with doped near5 contact and base with (opening hole recess))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/04 12:33
-	32	((bipolar bjt hbt hbjt) and base with doped near5 contact ) and (Sic silicon adj carbide ) not ((Sic silicon adj carbide) and ((bipolar bjt hbt hbjt) and base with doped near5 contact and base with (opening hole recess)) )	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/04 14:42

-	3	("5332912"   "5767540"   "6313488").PN.	USPAT	2004/05/04 12:36
-	33	((bipolar bjt hbt hbjt) and base with doped near5 contact ) and (Sic sigec sigce gesic gecsi csige cgesi silicon near3 carbide ) ) not ((Sic silicon adj carbide) and ((bipolar bjt hbt hbjt) and base with doped near5 contact and base with (opening hole recess)) )	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/04 14:46
-	54	((bipolar bjt hbt hbjt) and base with doped near5 contact ) and (Sic silicon adj carbide )	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/04 14:44
-	1	((bipolar bjt hbt hbjt) and base with doped near5 contact ) and (Sic sigec sigce gesic gecsi csige cgesi silicon near3 carbide ) not (Sic silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/04 14:45
-	55	((bipolar bjt hbt hbjt) and base with doped near5 contact ) and (Sic sigec sigce gesic gecsi csige cgesi silicon near3 carbide)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/04 14:46
-	1	((bipolar bjt hbt hbjt) and base with doped near5 contact ) and (Sic sigec sigce gesic gecsi csige cgesi silicon near3 carbide ) not ((bipolar bjt hbt hbjt) and base with doped near5 contact ) and (Sic silicon adj carbide ) )	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/04 17:25
-	374	(bipolar bjt hbt hbjt) and base near5 (heavily highly) adj doped and base with (opening etch\$ hole recess\$)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/04 17:28
-	74	(bipolar bjt hbt hbjt) and base near5 (heavily highly) adj doped and base with (opening etch\$ hole recess\$) and (sic compound adj semiconductor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/04 17:29
-	43	(bipolar bjt hbt hbjt) and base near5 (heavily highly) adj doped and base with (opening etch\$ hole recess\$) and (sic silicon near2 carbide)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/04 18:20
-	36	((bipolar bjt hbt hbjt) and base near5 (heavily highly) adj doped and base with (opening etch\$ hole recess\$) and (sic compound adj semiconductor)) not ((bipolar bjt hbt hbjt) and base near5 (heavily highly) adj doped and base with (opening etch\$ hole recess\$) and (sic silicon near2 carbide))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/05 16:24
-	1	i2l and sic	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/05 16:24
-	177	i2l	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/08 09:10
-	30	(Kordes-martin\$ Bartlow-Howard\$ Woodin-Richard\$).in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/08 09:16
-	379	(fairchild).as. and active	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/08 09:17
-	891	(fairchild).as. and semiconductor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/08 09:17



-	1	("20030039012").PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/08 13:25
-	1	("20010043663").PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/08 13:18
-	1	("20010030818").PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/08 13:18
-	1	("20030206686").PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/08 13:18
-	1	("20030210448").PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/08 15:16